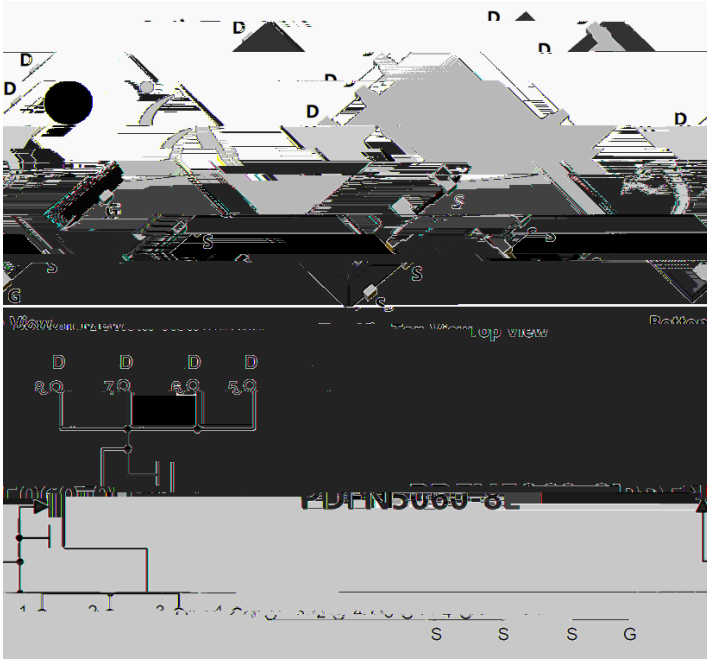




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	40V
I_D	60A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	Ø6.8m
100% EAS Tested	
100% j V_A	M

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	40	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	$T_A=25$ -	I_D	12	A
	$T_A=100$ -		8.4	
	$T_C=25$ -		60	
	$T_C=100$ -		42	
Pulsed Drain Current ^A		I_{DM}	240	A
Avalanche energy ^B		EAS	84	mJ
Total Power Dissipation ^C	$T_A=25$ -	P_D	2.7	W
	$T_A=100$ -		1.3	
	$T_C=25$ -		73	

	D	Steady-State	R_{JA}	46	55	- /W
Thermal Resistance Junction-to-Case		Steady-State	R_{JC}	1.7	2.04	

Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG60G04HHQ	F1	YJG60G04H	5000	10000	100000	13" reel



YJG60G04HHQ

Electrical Characteristics ($T_J=25$ unless otherwise noted)

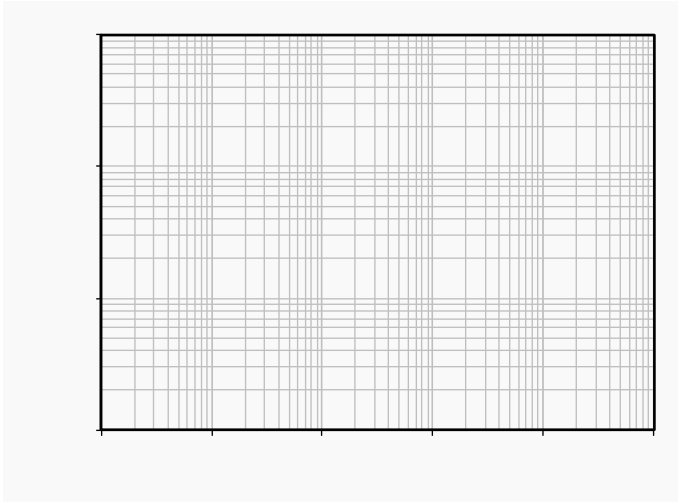
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						

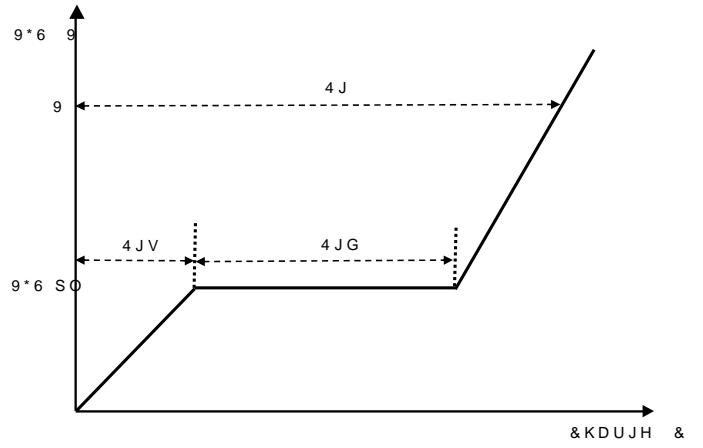
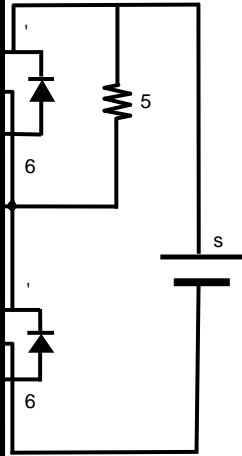




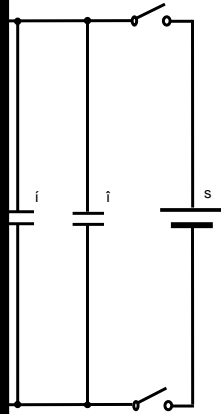
Figure 7. $R_{DS(on)}$ VS Drain Current

Figure 8. Forward characteristic





) L J A U P D W H & K D U J H U F X V W & : D Y H I R U P





< - * * + + 4

p'LVFODLPHU

7KH LQIRUPDWLRQ SUHVHQWHG LQ WKLV <DQJJKRX <DQJMEHFWHOLGEWORLD&R /ZZ \DQJMLH F

ULJKV